SKODENSHI AUK

SWITCHING REGULATOR APPLICATIONS

Features

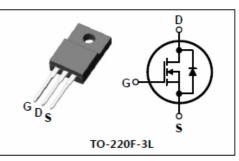
- High Voltage : BV_{DSS}=650V(Min.)
- Low Crss : Crss=10pF(Typ.)
- Low gate charge : Qg=21nC(Typ.)
- Low $R_{DS(on)}$: $R_{DS(on)}=1.4\Omega(Max.)$

Ordering Infor	mation	
Type NO	Marking	Package code
KMK0765F	KMK0765.	TO-220F-3L
KMK0765F(HF)	KMK0765.	T0-220F-3L

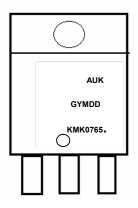
KMK0765F

Advanced N-Ch Power MOSFET

PIN Connection



Marking Diagram



• Da Lian

Column 1 : Manufacturer Column 2 : Production Information e.g.) GYMDD -. G : Factory management code -. YMDD : Date Code (year, month, date) Column 3 : Device Code

Absolute maximum ratings (Tc=25°C unless otherwise noted)

Characteristic	Symbol		Rating	Unit		
Drain-source voltage	Vdss		VDSS 650			
Gate-source voltage	Vgss		Vgss ±30		Vgss ±30	
Drain current (DC) *	ID	Tc=25℃	7	А		
	10	Tc=100°C	3.4	A		
Drain current (Pulsed)*	Ідм		28	A		
Power dissipation		Pd	40	W		
Avalanche current (Single) 2		IAS	7	A		
Single pulsed avalanche energy 2		Eas	201	mJ		
Avalanche current (Repetitive) ①		Iar	7	А		
Repetitive avalanche energy ①		Ear	14.7	mJ		
Junction temperature		Τı	150	°C		
Storage temperature range		Tstg	-55~150	C		

* Limited by maximum junction temperature

Chai	racteristic	Symbol	Тур.	Max	Unit
Thermal	Junction-case	Rth(J-C)	-	3.12	°C/W
resistance	Junction-ambient	Rth(J-A)	-	62.5	°C/W

Electrical Characteristics (Tc=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Drain-source breakdown voltage	BVDSS	ID=250uA, VGS=0V	650	-	-	V
Gate threshold voltage	VGS(th)	ID=250uA, VDS=VGS	2.0	-	4.0	V
Drain-source cut-off current	Idss	V _{DS} =650V, V _{GS} =0V	-	-	1	uA
Gate leakage current	Igss	$V_{DS}=0V, V_{GS}=\pm 30V$	-	-	± 100	nA
Drain-source on-resistance ④	RDS(on)	V _{GS} =10V, I _D =3.5A	-	1.2	1.4	Ω
Forward transfer conductance ④	g fs	V _{DS} =10V, I _D =3.5A	-	8.1	-	S
Input capacitance	Ciss	V _{GS} =0V, V _{DS} =25V f=1MHz	-	1006	1258	
Output capacitance	Coss		-	98	123	pF
Reverse transfer capacitance	Crss		-	10	15	
Turn-on delay time	td(on)		-	18	-	
Rise time	tr	V _{DD} =300V, I _D =7.0A R _G =25Ω ③④	-	19	-	
Turn-off delay time	td(off)		-	72	-	nc
Fall time	tr		-	28	-	ns
Total gate charge	Qg	VDs=520V, VGs=10V	-	21	27	
Gate-source charge	Qgs	ID=7.0A 34	-	6	-	nC
Gate-drain charge	Qgd		-	5	-	

Source-Drain Diode Ratings and Characteristics (Tc=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Source current (DC)	Is	Integral reverse diode	-	-	7	٨
Source current (Pulsed) ①	Isм	in the MOSFET	-	-	28	A
Forward voltage ④	Vsd	V _G s=0V, Is=7.0A	-	-	1.4	V
Reverse recovery time	trr	Is=7.0A, V _{GS} =0V	-	365	-	ns
Reverse recovery charge	Qrr	dIF/dt=100A/us	-	3.4	-	uC

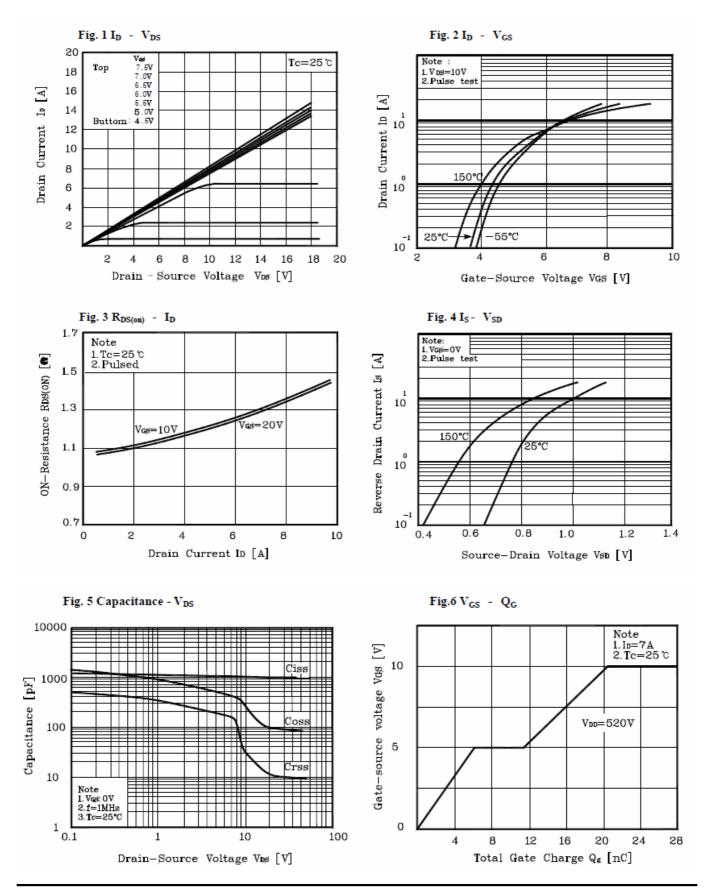
Note ;

① Repetitive rating : Pulse width limited by maximum junction temperature

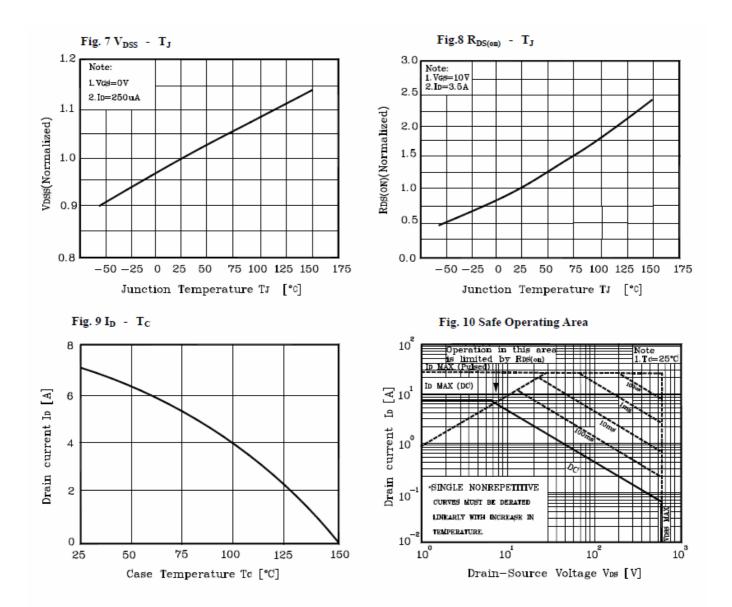
② L=7.6mH, IAs=7.0A, VDD=50V, RG=25Ω, Starting TJ=25°C

③ Pulse Test : Pulse width <300us, Duty cycle <2%

④ Essentially independent of operating temperature



Electrical Characteristic Curves



Electrical Characteristic Curves

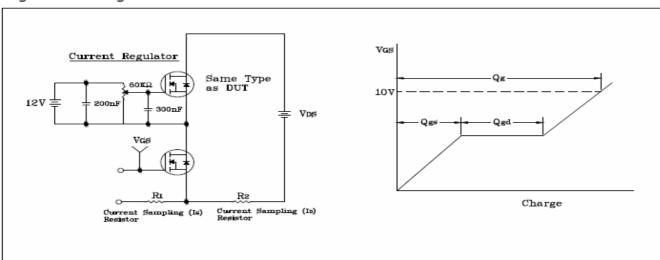
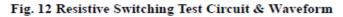


Fig. 11 Gate Charge Test Circuit & Waveform



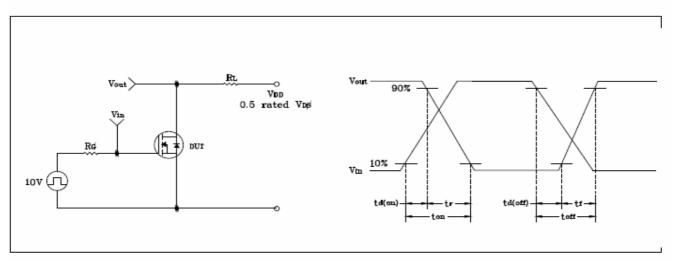
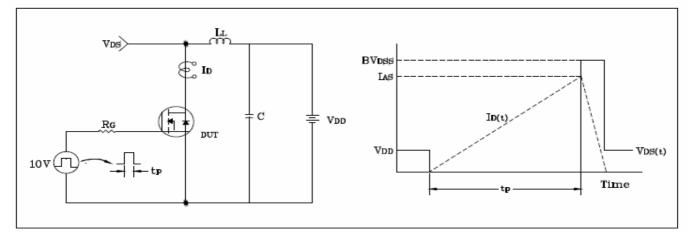


Fig. 13 EAS Test Circuit & Waveform



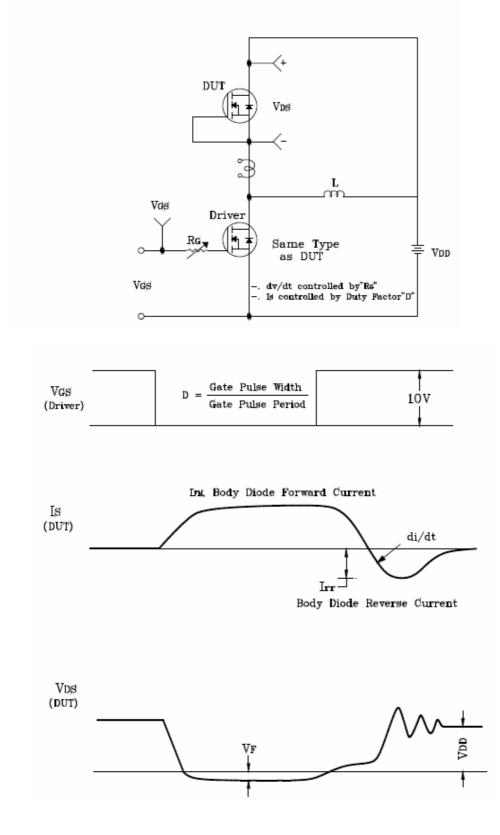
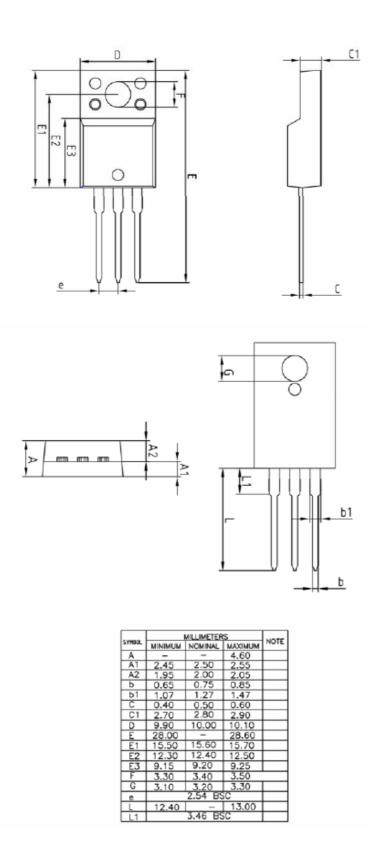


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform

Outline Dimension

unit: mm



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